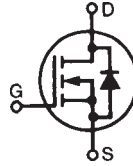


# X3-Class HiPerFET™ Power MOSFET

**IXFP80N25X3**  
**IXFQ80N25X3**  
**IXFH80N25X3**

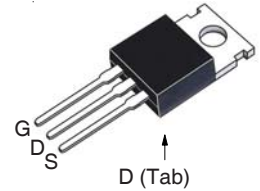
**V<sub>DSS</sub> = 250V**  
**I<sub>D25</sub> = 80A**  
**R<sub>DS(on)</sub> ≤ 16mΩ**

N-Channel Enhancement Mode  
Avalanche Rated

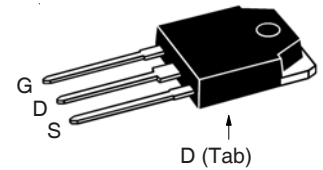


Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	250	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C, R <sub>GS</sub> = 1MΩ	250	V
V <sub>GSS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	80	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, Pulse Width Limited by T <sub>JM</sub>	220	A
I <sub>A</sub>	T <sub>C</sub> = 25°C	40	A
E <sub>AS</sub>	T <sub>C</sub> = 25°C	1.2	J
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C	20	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	390	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering	300	°C
T <sub>SOLD</sub>	1.6 mm (0.062in.) from Case for 10s	260	°C
M <sub>d</sub>	Mounting Torque	1.13 / 10	Nm/lb.in
Weight	TO-220	3.0	g
	TO-3P	5.5	g
	TO-247	6.0	g

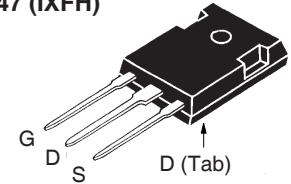
## TO-220 (IXFP)



## TO-3P (IXFQ)



## TO-247 (IXFH)



G = Gate      D = Drain  
S = Source    Tab = Drain

## Features

- International Standard Packages
- Low R<sub>DS(ON)</sub> and Q<sub>G</sub>
- Avalanche Rated
- Low Package Inductance

## Advantages

- High Power Density
- Easy to Mount
- Space Savings

## Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions (T <sub>J</sub> = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	250		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1.5mA	2.5		4.5 V
I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100 nA
I <sub>DSS</sub>	V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0V T <sub>J</sub> = 125°C			5 μA 350 μA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.5 • I <sub>D25</sub> , Note 1		13	16 mΩ

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	38	64	S
$R_{Gi}$	Gate Input Resistance		1.6	$\Omega$
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		5430	pF
$C_{oss}$			890	pF
$C_{rss}$			1.6	pF
<b>Effective Output Capacitance</b>				
$C_{o(er)}$	Energy related	$V_{GS} = 0\text{V}$ $V_{DS} = 0.8 \cdot V_{DSS}$	320	pF
$C_{o(tr)}$	Time related		1410	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 5\Omega$ (External)		30	ns
$t_r$			17	ns
$t_{d(off)}$			65	ns
$t_f$			8	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		83	nC
$Q_{gs}$			27	nC
$Q_{gd}$			24	nC
$R_{thJC}$	TO-220 TO-247& TO-3P			0.32 $^\circ\text{C/W}$
$R_{thCS}$			0.50 0.25	$^\circ\text{C/W}$ $^\circ\text{C/W}$

#### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
$I_S$	$V_{GS} = 0\text{V}$			80 A
$I_{SM}$	Repetitive, pulse Width Limited by $T_{JM}$			320 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1			1.4 V
$t_{rr}$	$I_F = 40\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		120	ns
$Q_{RM}$			600	nC
$I_{RM}$			10	A

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

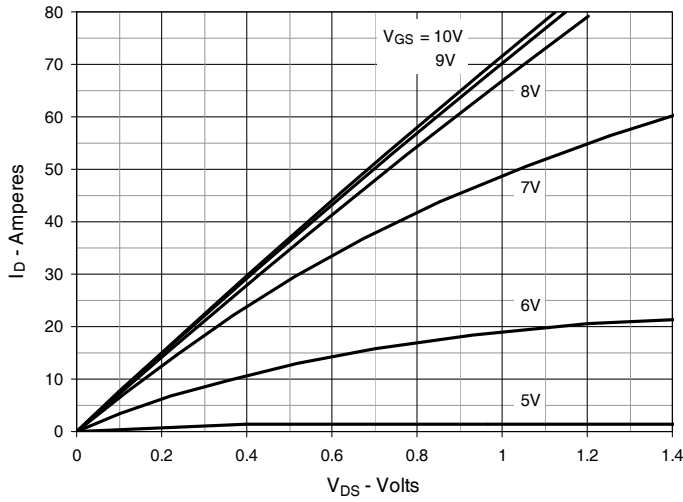


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

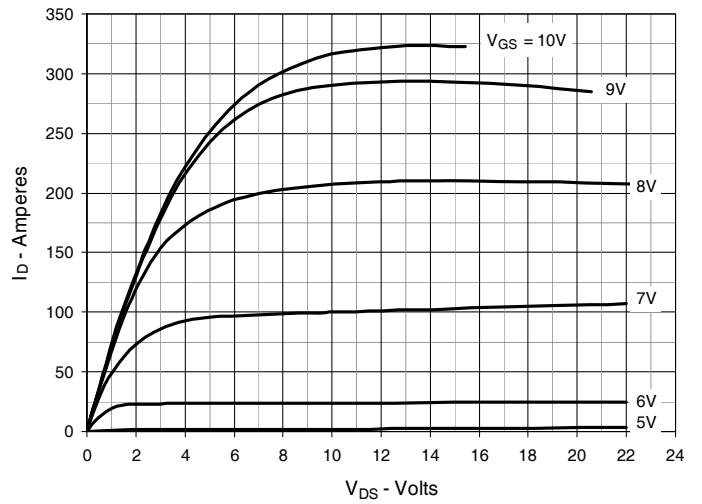


Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$

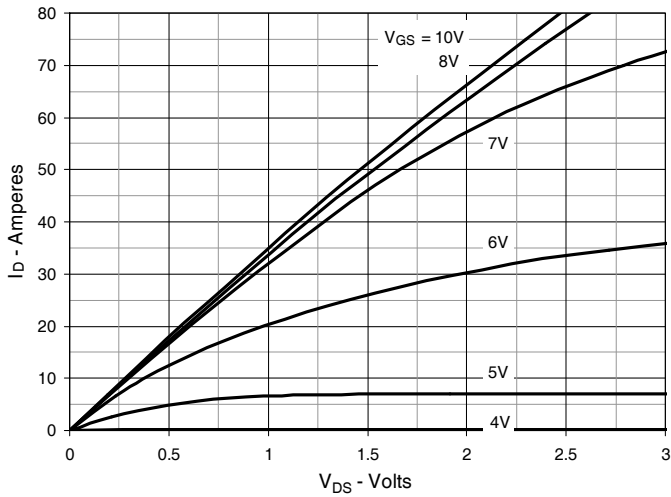


Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 40\text{A}$  Value vs. Junction Temperature

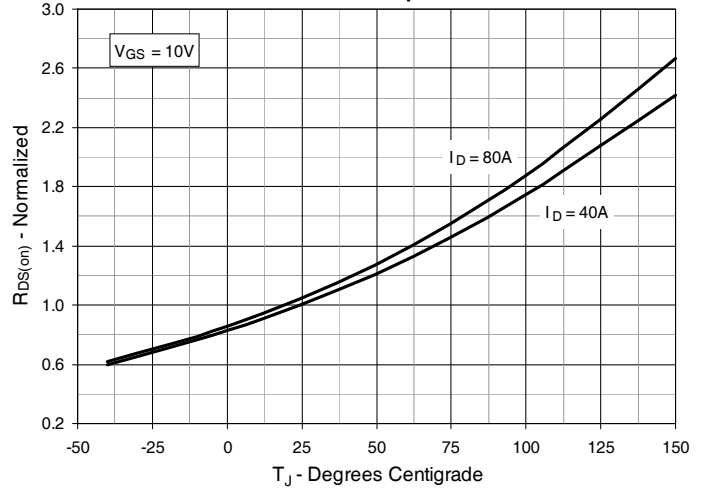


Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 40\text{A}$  Value vs. Drain Current

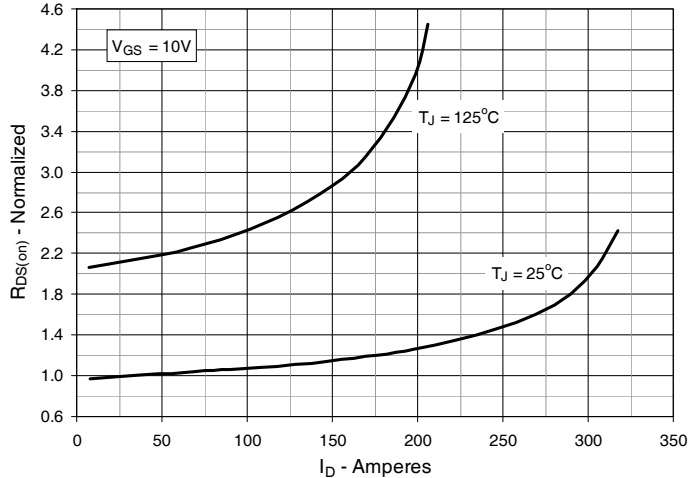


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

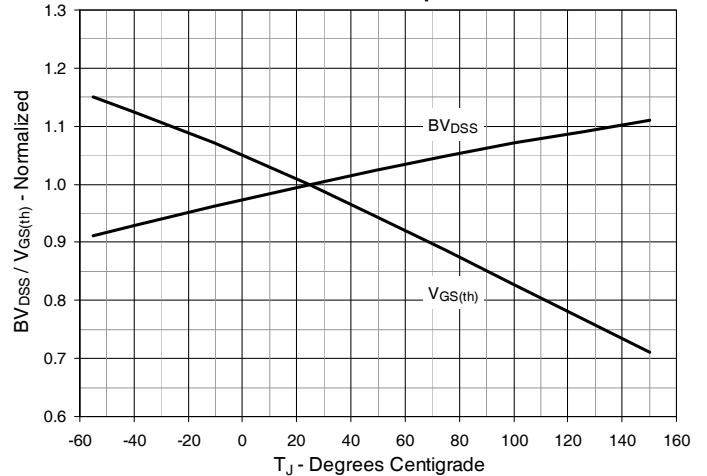


Fig. 7. Maximum Drain Current vs. Case Temperature

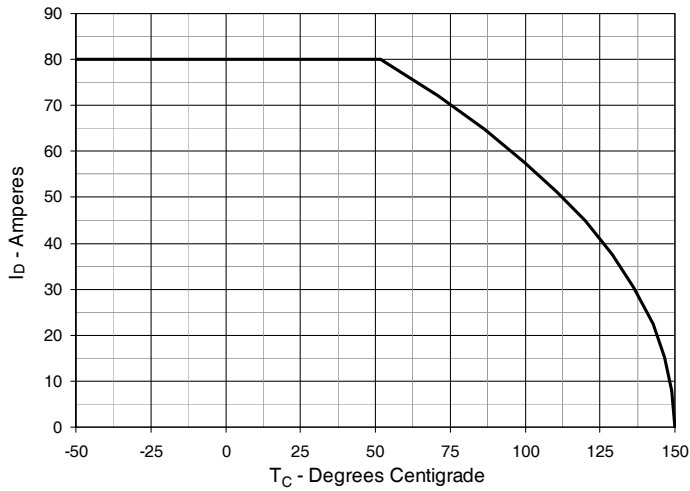


Fig. 8. Input Admittance

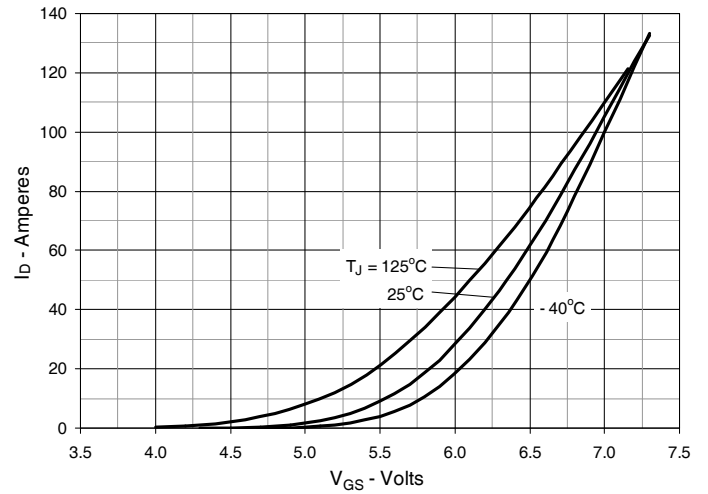


Fig. 9. Transconductance

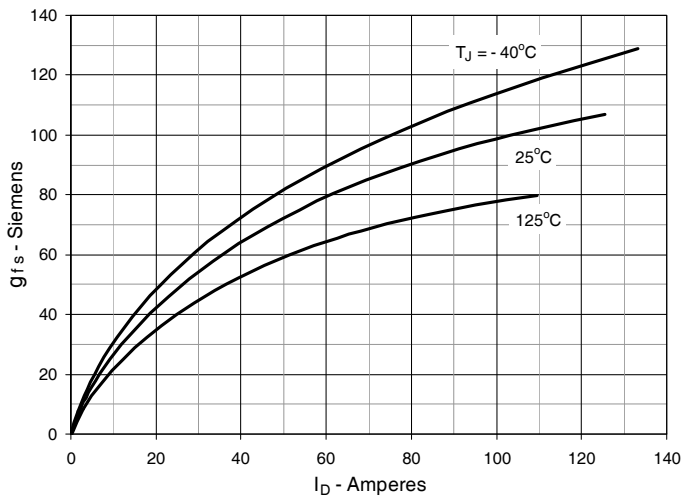


Fig. 10. Forward Voltage Drop of Intrinsic Diode

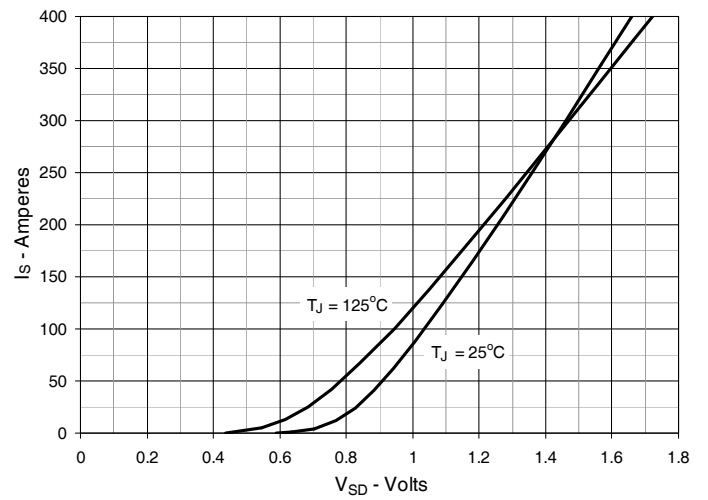


Fig. 11. Gate Charge

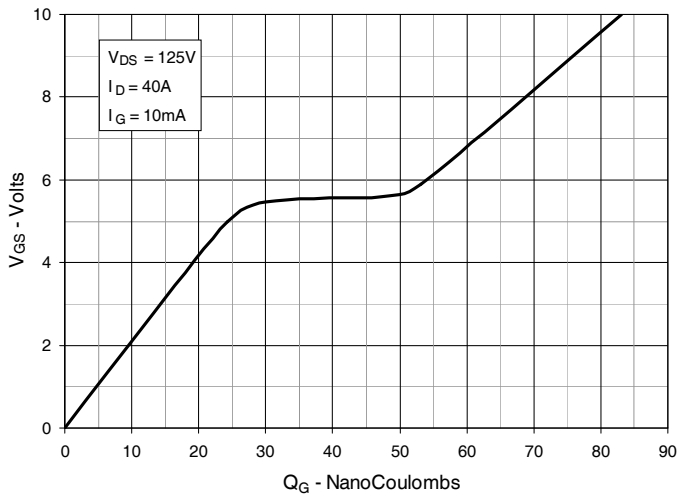


Fig. 12. Capacitance

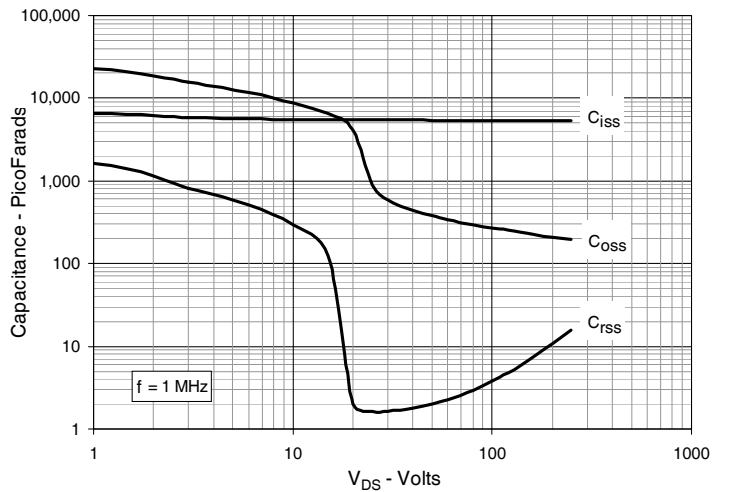


Fig. 13. Output Capacitance Stored Energy

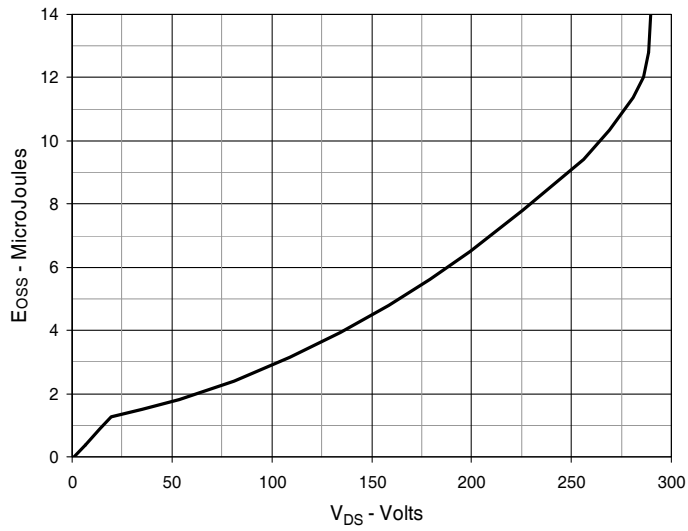


Fig. 14. Forward-Bias Safe Operating Area

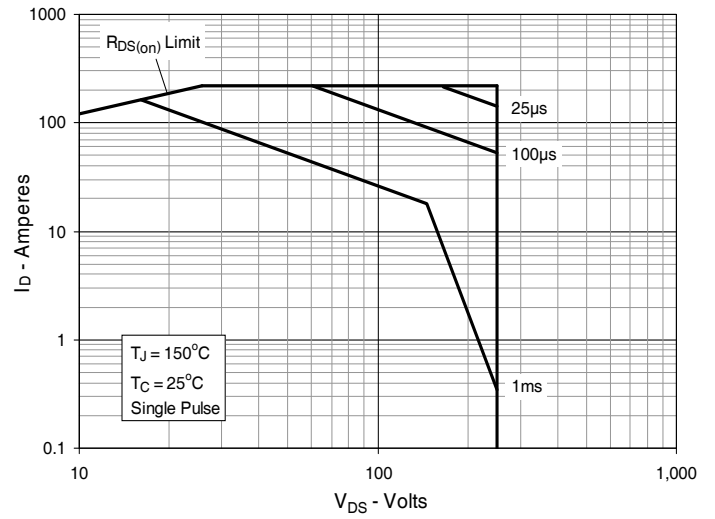
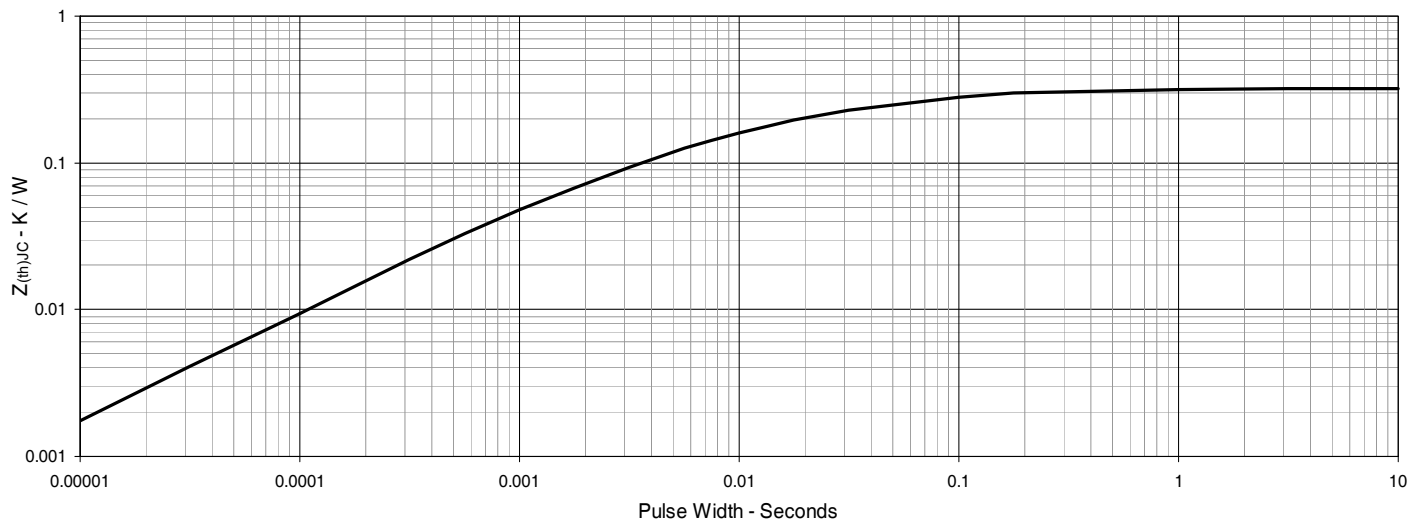
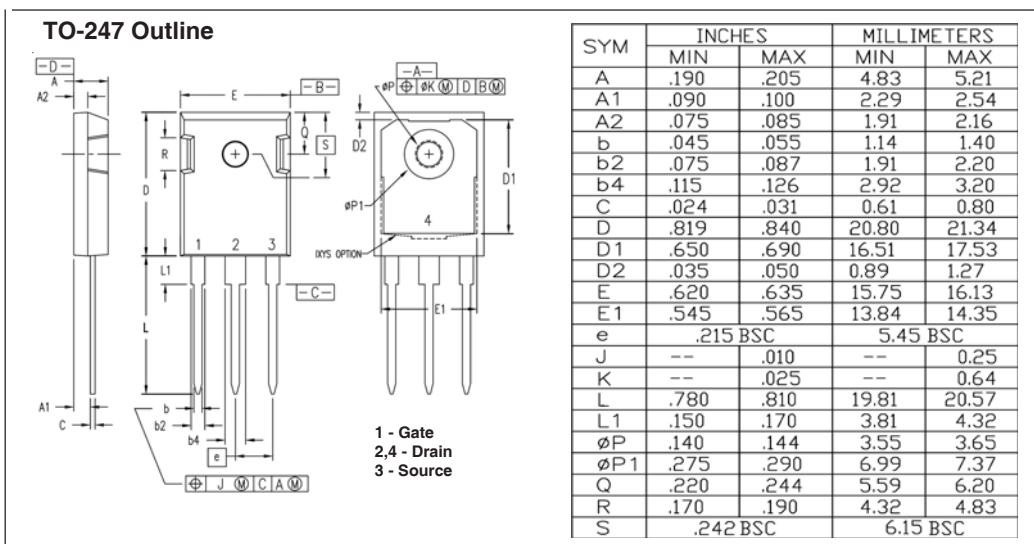
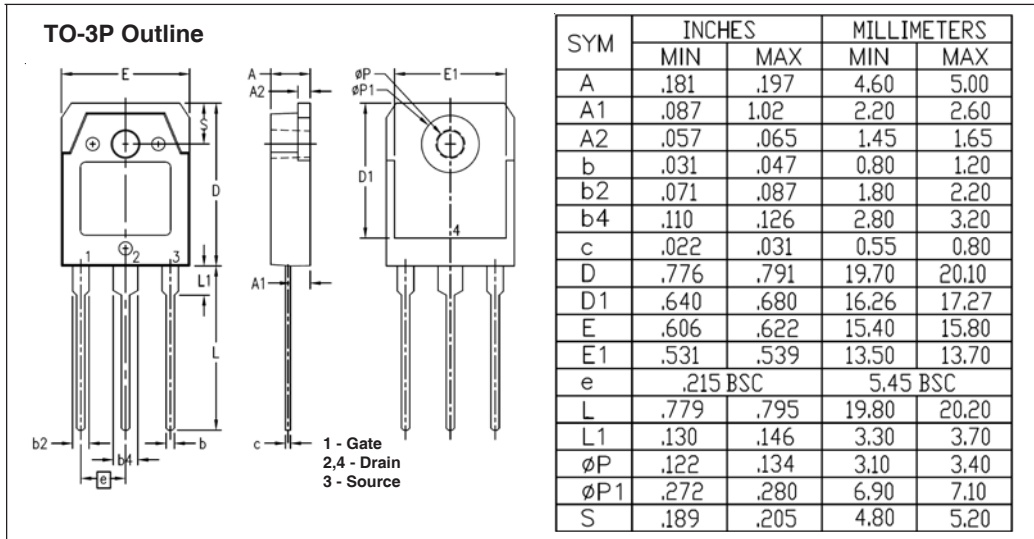
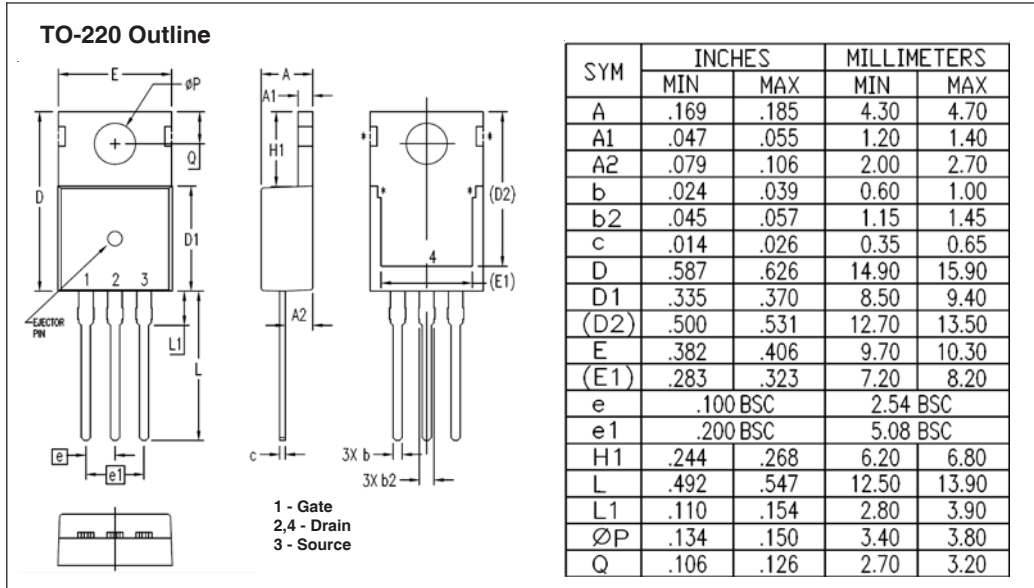


Fig. 15. Maximum Transient Thermal Impedance







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